SILICON PNP TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

2SA 1273

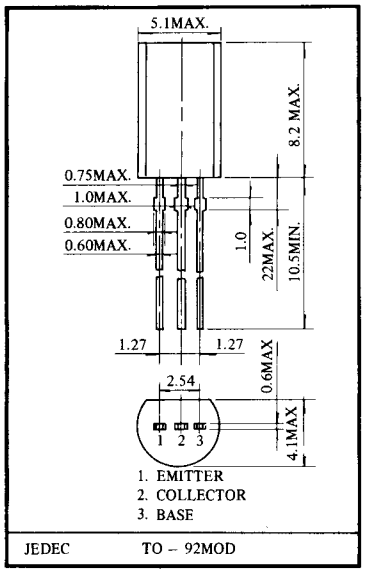
APPLICATIONS

- Audio Power Amplifier Applications.

FEATURES

- Complementary to 2SC 3205 and 3 Watts Output Applications.

Unit in mm



MAXIMUM RATINGS (Ta = 25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−30	V
Collector-Emitter Voltage	V_{CEO}	−30	V
Emitter-Base Voltage	V_{EBO}	− 5	V
Collector Current	I_C	−2	A

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	2	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_j	150	℃
Storage Temperature	Tstg	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta = 25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = −30V, I_E = 0	−	−	−100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = −5V, I_C = 0	−	−	−100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = −10mA, I_B = 0	−30	−	−	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = −1mA, I_C = 0	−5	−	−	V
DC Current Gain	h_{FE}	V_{CE} = −2V, I_C = −500mA	100	−	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = −1.5A, I_B = −0.03A	−	−	−2.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = −2V, I_C = −500mA	−	−	−1.0	V
Transition Frequency	f_T	V_{CE} = −2V, I_C = −500mA	−	120	−	MHz
Collector Output Capacitiance	C_{ob}	V_{CB} = −10V, I_E = 0, f = 1MHz	−	48	−	pF

NOTE: According to h_{FE}, Classified as follows.

O	100 - 200	Y	160 - 320

KEC